

Si550

REVISION D

VOLTAGE-CONTROLLED CRYSTAL OSCILLATOR (VCXO) 10 MHz to 1.4 GHz

Features

- Available with any frequency from
 Internal fixed crystal frequency 10 to 945 MHz and select frequencies to 1.4 GHz
- 3rd generation DSPLL[®] with superior jitter performance (0.5 ps)
- 3x better temperature stability than SAW-based oscillators
- Excellent PSRR performance
- ensures high reliability and low aging
- Available CMOS, LVPECL, LVDS, and CML outputs
- 3.3, 2.5, and 1.8 V supply options Industry-standard 5 x 7 mm
- package and pinout
- Pb-free/RoHS-compliant

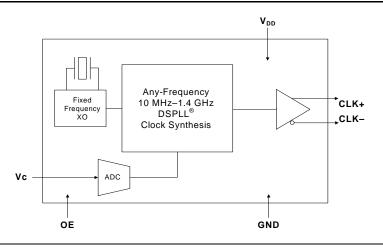
Applications

- SONET/SDH
- **xDSL**
- 10 GbE LAN/WAN
- Low-jitter clock generation
- Optical modules
- Clock and data recovery

Description

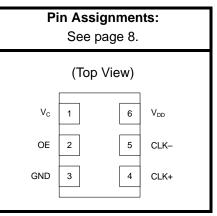
The Si550 VCXO utilizes Silicon Laboratories' advanced DSPLL® circuitry to provide a low-jitter clock at high frequencies. The Si550 supports any frequency from 10 to 945 MHz and select frequencies to 1417 MHz. Unlike traditional VCXOs, where a different crystal is required for each output frequency, the Si550 uses one fixed crystal to provide a wide range of output frequencies. This IC-based approach allows the crystal resonator to provide exceptional frequency stability and reliability. In addition, DSPLL clock synthesis provides superior supply noise rejection, simplifying the task of generating low-jitter clocks in noisy environments typically found in communication systems. The Si550 IC-based VCXO is factory-configurable for a wide variety of user specifications, including frequency, supply voltage, output format, tuning slope, and temperature stability. Specific configurations are factory programmed at time of shipment, thereby eliminating the long lead times associated with custom oscillators.

Functional Block Diagram









1. Electrical Specifications

Table 1. Recommended Operating Conditions

Parameter	Symbol	Test Condition	Min	Тур	Мах	Units
Supply Voltage ¹	V _{DD}	3.3 V option	2.97	3.3	3.63	V
		2.5 V option	2.25	2.5	2.75	V
	-	1.8 V option	1.71	1.8	1.89	V
Supply Current	I _{DD}	Output enabled		400	100	
		LVPECL		120	130	
		CML	—	108	117	mA
		LVDS	—	99	108	
		CMOS	—	90	98	
		tristate mode	—	60	75	mA
Output Enable (OE) ²		V _{IH}	0.75 x V _{DD}	—	—	V
		V _{IL}	—	_	0.5	V
Operating Temperature Range	T _A		-40		85	°C
Notes:	1					1

1. Selectable parameter specified by part number. See 3. "Ordering Information" on page 9 for further details.

2. OE pin includes a 17 k Ω resistor to V_{DD}.

Table 2. V_C Control Voltage Input

Parameter	Symbol	Test Condition	Min	Тур	Max	Units
Control Voltage Tuning Slope ^{1,2,3}	K _V	10 to 90% of V _{DD}		33	_	
			—	45	—	
			—	90	—	ppm/V
			—	135	—	ppin/v
			—	180	—	
			—	356	—	
Control Voltage Linearity ⁴	L _{VC}	BSL	-5	±1	+5	%
		Incremental	-10	±5	+10	%
Modulation Bandwidth	BW		9.3	10.0	10.7	kHz
V _C Input Impedance	Z _{VC}		500	—	_	kΩ
Nominal Control Voltage	V _{CNOM}	@ f _O	—	V _{DD} /2	_	V
Control Voltage Tuning Range	V _C		0		V _{DD}	V

Notes:

2

1. Positive slope; selectable option by part number. See 3. "Ordering Information" on page 9.

For best jitter and phase noise performance, always choose the smallest K_V that meets the application's minimum APR requirements. See "AN266: VCXO Tuning Slope (K_V), Stability, and Absolute Pull Range (APR)" for more information.

3. K_V variation is ±10% of typical values.

BSL determined from deviation from best straight line fit with V_C ranging from 10 to 90% of V_{DD}. Incremental slope determined with V_C ranging from 10 to 90% of V_{DD}.



Table 3. CLK± Output Frequency Characteristics

Parameter	Symbol	Test Condition	Min	Тур	Max	Units
Nominal Frequency ^{1,2,3}	f _O	LVDS/CML/LVPECL	10	—	945	MHz
		CMOS	10		160	MHz
Temperature Stability ^{1,4}		T _A = -40 to +85 °C	-20	—	+20	
			-50	—	+50	ppm
			-100	—	+100	
Absolute Pull Range ^{1,4}	APR		±12		±375	ppm
Aging		Frequency drift over first year.	_		±3	nnm
		Frequency drift over 15 year life.	_	—	±10	ppm
Power up Time ⁵	tosc		_	—	10	ms
Nataa						

Notes:

1. See Section 3. "Ordering Information" on page 9 for further details.

2. Specified at time of order by part number. Also available in frequencies from 970 to 1134 MHz and 1213 to 1417 MHz.

Nominal output frequency set by V_{CNOM} = V_{DD}/2.
 Selectable parameter specified by part number.

5. Time from power up or tristate mode to f_{O} .

Table 4. CLK± Output Levels and Symmetry

Parameter	Symbol	Test Condition	Min	Тур	Max	Units
LVPECL Output Option ¹	Vo	mid-level	V _{DD} - 1.42		V _{DD} – 1.25	V
	V _{OD}	swing (diff)	1.1		1.9	V _{PP}
	V _{SE}	swing (single-ended)	0.55	_	0.95	V _{PP}
LVDS Output Option ²	V _O	mid-level	1.125	1.20	1.275	V
	V _{OD}	swing (diff)	0.5	0.7	0.9	V _{PP}
		2.5/3.3 V option mid-level	—	V _{DD} – 1.30	—	V
CML Output Option ²	Vo	1.8 V option mid-level	—	$V_{DD} - 0.36$	_	V
	V	2.5/3.3 V option swing (diff)	1.10	1.50	1.90	V _{PP}
	V _{OD}	1.8 V option swing (diff)	0.35	0.425	0.50	V _{PP}
CMOS Output Option ³	V _{OH}	I _{OH} = 32 mA	0.8 x V _{DD}		V _{DD}	V
	V _{OL}	I _{OL} = 32 mA	—		0.4	V
Rise/Fall time (20/80%)	t _{R,} t _F	LVPECL/LVDS/CML	—		350	ps
		CMOS with $C_L = 15 \text{ pF}$	—	1		ns
Symmetry (duty cycle)	SYM	LVPECL: V _{DD} - 1.3 V (diff) LVDS: 1.25 V (diff) CMOS: V _{DD} /2	45		55	%

Notes:

1. 50 Ω to V_DD – 2.0 V.

2. $R_{term} = 100 \Omega$ (differential).

3. $C_L = 15 \, \text{pF}$



Table 5. CLK± Output Phase Jitter

Parameter	Symbol	Test Condition	Min	Тур	Max	Units
Phase Jitter (RMS) ^{1,2,3}	φJ	Kv = 33 ppm/V				
for $F_{OUT} \ge 500 \text{ MHz}$		12 kHz to 20 MHz (OC-48)	—	0.26	—	ps
		50 kHz to 80 MHz (OC-192)	—	0.26	—	
		Kv = 45 ppm/V				
		12 kHz to 20 MHz (OC-48)	_	0.27	—	ps
		50 kHz to 80 MHz (OC-192)	—	0.26	—	
		Kv = 90 ppm/V				
		12 kHz to 20 MHz (OC-48)	_	0.32	—	ps
		50 kHz to 80 MHz (OC-192)	—	0.26	—	
		Kv = 135 ppm/V				
		12 kHz to 20 MHz (OC-48)	_	0.40	—	ps
		50 kHz to 80 MHz (OC-192)	_	0.27	—	
		Kv = 180 ppm/V				
		12 kHz to 20 MHz (OC-48)	_	0.49	—	ps
		50 kHz to 80 MHz (OC-192)	—	0.28	—	
		Kv = 356 ppm/V				
		12 kHz to 20 MHz (OC-48)	_	0.87	—	ps
		50 kHz to 80 MHz (OC-192)	_	0.33	—	

Notes:

1. Refer to AN255, AN256, and AN266 for further information.

2. For best jitter and phase noise performance, always choose the smallest K_V that meets the application's minimum APR requirements. See "AN266: VCXO Tuning Slope (K_V), Stability, and Absolute Pull Range (APR)" for more information.

3. See "AN255: Replacing 622 MHz VCSO devices with the Si550 VCXO" for comparison highlighting power supply rejection (PSR) advantage of Si55x versus SAW-based solutions.

- 4. Max jitter for LVPECL output with V_C=1.65V, V_{DD}=3.3V, 155.52 MHz. 5. Max offset frequencies: 80 MHz for F_{OUT} \geq 250 MHz, 20 MHz for 50 MHz \leq F_{OUT} <250 MHz,
- 2 MHz for 10 MHz \leq F_{OUT} <50 MHz.



Table 5. CLK± Output Phase Jitter (Continued)

Parameter	Symbol	Test Condition	Min	Тур	Max	Units
Phase Jitter (RMS) ^{1,2,3,4,5}	фj	Kv = 33 ppm/V				
for F _{OUT} of 125 to 500 MHz		12 kHz to 20 MHz (OC-48)	_	0.37	—	ps
		50 kHz to 80 MHz (OC-192)	—	0.33	—	
		Kv = 45 ppm/V				
		12 kHz to 20 MHz (OC-48)	—	0.37	0.4	ps
		50 kHz to 80 MHz (OC-192)	—	0.33	—	
		Kv = 90 ppm/V				
		12 kHz to 20 MHz (OC-48)	—	0.43	—	ps
		50 kHz to 80 MHz (OC-192)	—	0.34	—	
		Kv = 135 ppm/V				
		12 kHz to 20 MHz (OC-48)	—	0.50	—	ps
		50 kHz to 80 MHz (OC-192)	—	0.34	—	
		Kv = 180 ppm/V				
		12 kHz to 20 MHz (OC-48)	—	0.59	—	ps
		50 kHz to 80 MHz (OC-192)	—	0.35	—	
		Kv = 356 ppm/V				
		12 kHz to 20 MHz (OC-48)	—	1.00	—	ps
		50 kHz to 80 MHz (OC-192)	—	0.39	—	

Notes:

1. Refer to AN255, AN256, and AN266 for further information.

2. For best jitter and phase noise performance, always choose the smallest K_V that meets the application's minimum APR requirements. See "AN266: VCXO Tuning Slope (K_V), Stability, and Absolute Pull Range (APR)" for more information. 3. See "AN255: Replacing 622 MHz VCSO devices with the Si550 VCXO" for comparison highlighting power supply

rejection (PSR) advantage of Si55x versus SAW-based solutions.

4. Max jitter for LVPECL output with $V_C=1.65V$, $V_{DD}=3.3V$, 155.52 MHz. 5. Max offset frequencies: 80 MHz for $F_{OUT} \ge 250$ MHz, 20 MHz for 50 MHz $\le F_{OUT} <250$ MHz, 2 MHz for 10 MHz $\le F_{OUT} <50$ MHz.



Table 5. CLK± Output Phase Jitter (Continued)

Parameter	Symbol	Test Condition	Min	Тур	Max	Units
Phase Jitter (RMS) ^{1,2,5} for F _{OUT} 10 to 160 MHz CMOS Output Only	фј	Kv = 33 ppm/V 12 kHz to 20 MHz (OC-48) 50 kHz to 20 MHz		0.63 0.62		ps
		Kv = 45 ppm/V 12 kHz to 20 MHz (OC-48) 50 kHz to 20 MHz	_	0.63 0.62		ps
		Kv = 90 ppm/V 12 kHz to 20 MHz (OC-48) 50 kHz to 20 MHz		0.67 0.66		ps
		Kv = 135 ppm/V 12 kHz to 20 MHz (OC-48) 50 kHz to 20 MHz	_	0.74 0.72		ps
		Kv = 180 ppm/V 12 kHz to 20 MHz (OC-48) 50 kHz to 20 MHz		0.83 0.8		ps
		Kv = 356 ppm/V 12 kHz to 20 MHz (OC-48) 50 kHz to 20 MHz		1.26 1.2		ps

Notes:

- 1. Refer to AN255, AN256, and AN266 for further information.
- 2. For best jitter and phase noise performance, always choose the smallest K_V that meets the application's minimum APR requirements. See "AN266: VCXO Tuning Slope (K_V), Stability, and Absolute Pull Range (APR)" for more information.
- 3. See "AN255: Replacing 622 MHz VCSO devices with the Si550 VCXO" for comparison highlighting power supply rejection (PSR) advantage of Si55x versus SAW-based solutions.
- 4. Max jitter for LVPECL output with V_C =1.65V, V_{DD} =3.3V, 155.52 MHz.
- 5. Max offset frequencies: 80 MHz for $F_{OUT} \ge 250$ MHz, 20 MHz for 50 MHz $\le F_{OUT} <250$ MHz, 2 MHz for 10 MHz $\le F_{OUT} <50$ MHz.

Table 6. CLK± Output Period Jitter

Parameter	Symbol	Test Condition	Min	Тур	Мах	Units
Period Jitter*	J _{PER}	RMS	_	2		ps
		Peak-to-Peak	_	14	_	
*Note: Any output mode, including C	CMOS, LVPI	ECL, LVDS, CML. N = 1000 cycles.	Refer to AN	279 for furt	her informa	ation.



Offset Frequency	74.25 MHz	155.52 MHz	491.52 MHz	622.08 MHz	Units
	90 ppm/V	45 ppm/V	45 ppm/V	135 ppm/V	
	LVPECL	LVPECL	LVPECL	LVPECL	
100 Hz	-87	-86	-75	-65	
1 kHz	-114	-111	-100	-90	
10 kHz	-132	-128	-116	-109	
100 kHz	-142	-133	-124	-121	dBc/Hz
1 MHz	-148	-144	-135	-134	
10 MHz	-150	-147	-146	-146	
100 MHz	n/a	n/a	-147	-147	

Table 7. CLK± Output Phase Noise (Typical)

Table 8. Environmental Compliance

The Si550 meets the following qualification test requirements.

Parameter	Conditions/Test Method
Mechanical Shock	MIL-STD-883, Method 2002
Mechanical Vibration	MIL-STD-883, Method 2007
Solderability	MIL-STD-883, Method 203
Gross & Fine Leak	MIL-STD-883, Method 1014
Resistance to Solder Heat	MIL-STD-883, Method 2036
Moisture Sensitivity Level	J-STD-020, MSL 1
Contact Pads	J-STD-020, MSL 1

Table 9. Absolute Maximum Ratings¹

Parameter	Symbol	Rating	Units
Maximum Operating Temperature	T _{AMAX}	85	٥C
Supply Voltage, 1.8 V Option	V _{DD}	-0.5 to +1.9	V
Supply Voltage, 2.5/3.3 V Option	V _{DD}	-0.5 to +3.8	V
Input Voltage	VI	–0.5 to V _{DD} + 0.3	V
Storage Temperature	Τ _S	-55 to +125	٥C
ESD Sensitivity (HBM, per JESD22-A114)	ESD	2500	V
Soldering Temperature (Pb-free profile) ²	T _{PEAK}	260	٥C
Soldering Temperature Time @ T _{PEAK} (Pb-free profile) ²	t _P	20–40	seconds
N1. (и	

Notes:

1. Stresses beyond those listed in Absolute Maximum Ratings may cause permanent damage to the device. Functional operation or specification compliance is not implied at these conditions. Exposure to maximum rating conditions for extended periods may affect device reliability.

2. The device is compliant with JEDEC J-STD-020C. Refer to Si5xx Packaging FAQ available for download from www.silabs.com/VCXO for further information, including soldering profiles.



2. Pin Descriptions

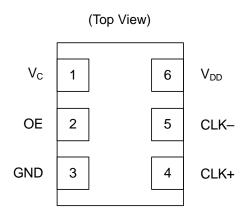


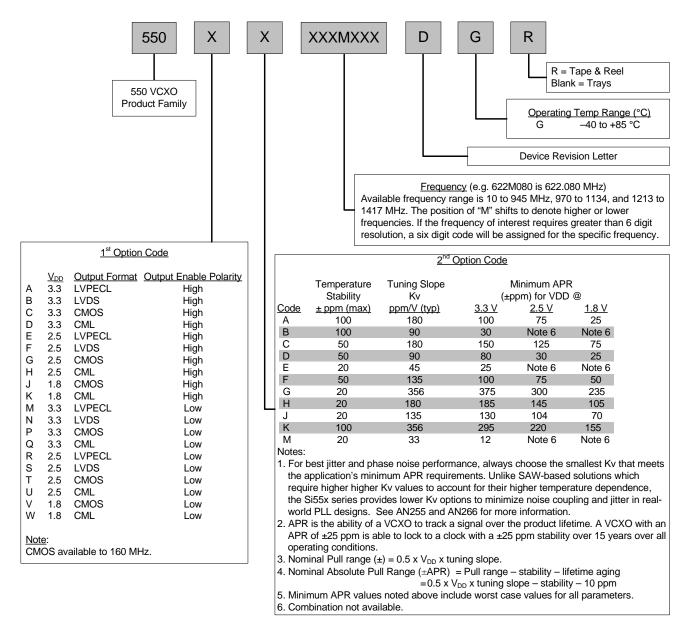
Table 10. Si550 Pin Descriptions

Pin	Name	Туре	Function				
1	V _C	Analog Input	Control Voltage				
2	OE*	Input	Output Enable (Polarity = High): 0 = clock output disabled (outputs tri-stated) 1 = clock output enabled Output Enable (Polarity = Low): 0 = clock output enabled 1 = clock output disabled (outputs tri-stated)				
3	GND	Ground	Electrical and Case Ground				
4	CLK+	Output	Oscillator Output				
5	CLK– (N/A for CMOS)	Output	Complementary Output (N/C for CMOS, make no external connection)				
6	V _{DD}	Power	Power Supply Voltage				
	*Note: OE includes 17 kΩ pullup resistor to V _{DD} . See Section 3. "Ordering Information" on page 9 for details on OE polarity ordering options.						



3. Ordering Information

The Si550 supports a variety of options including frequency, temperature stability, tuning slope, output format, and V_{DD} . Specific device configurations are programmed into the Si550 at time of shipment. Configurations are specified using the Part Number Configuration chart shown below. Silicon Labs provides a web browser-based part number configuration utility to simplify this process. Refer to www.silabs.com/VCXOPartNumber to access this tool and for further ordering instructions. The Si550 VCXO series is available in an industry-standard, RoHS compliant, lead-free, 6-pad, 5 x 7 mm package. Tape and reel packaging is an ordering option.



Example Part Number: 550AF622M080DGR is a 5 x 7 mm VCXO in a 6 pad package. The nominal frequency is 622.080 MHz, with a 3.3 V supply, LVPECL output, and Output Enable active high polarity. Temperature stability is specified as ±50 ppm and the tuning slope is 135 ppm/V. The part is specified for a -40 to +85 C° ambient temperature range operation and is shipped in tape and reel format.

Figure 1. Part Number Convention



4. Package Outline and Suggested Pad Layout

Figure 2 illustrates the package details for the Si550. Table 11 lists the values for the dimensions shown in the illustration.

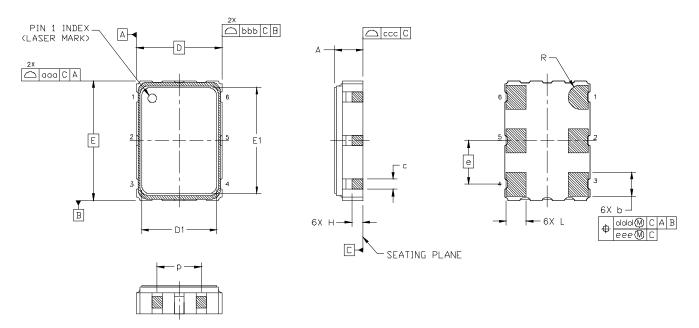


Figure 2. Si550 Outline Diagram

Dimension Min Nom Max A 1.50 1.65 1.80 b 1.30 1.40 1.50 c 0.50 0.60 0.70 D 5.00 BSC D1 4.30 4.40 4.50 e 2.54 BSC. E 7.00 BSC. E1 6.10 6.20 6.30 H 0.55 0.65 0.75 L 1.17 1.27 1.37 p 1.80 — 2.60 R 0.70 REF aaa 0.15 bbb 0.15 0.10 0.10 ddd 0.10 0.50 0.50				
b 1.30 1.40 1.50 c 0.50 0.60 0.70 D 5.00 BSC D1 4.30 4.40 4.50 e 2.54 BSC. E 7.00 BSC. E1 6.10 6.20 6.30 H 0.55 0.65 0.75 L 1.17 1.27 1.37 p 1.80 — 2.60 R 0.70 REF aaa 0.15 bbb 0.15 0.10 0.10 ddd 0.10 0.10 0.10	Dimension	Min	Nom	Max
c 0.50 0.60 0.70 D 5.00 BSC D1 4.30 4.40 4.50 e 2.54 BSC. E 7.00 BSC. E1 6.10 6.20 6.30 H 0.55 0.65 0.75 L 1.17 1.27 1.37 p 1.80 — 2.60 R 0.70 REF aaa 0.15 bbb 0.15 0.10 0.10	A	1.50	1.65	1.80
D 5.00 BSC D1 4.30 4.40 4.50 e 2.54 BSC. E E 7.00 BSC. 6.30 H 0.55 0.65 0.75 L 1.17 1.27 1.37 p 1.80 — 2.60 R 0.70 REF aaa 0.15 bbb 0.15 0.10 0.10	b	1.30	1.40	1.50
D1 4.30 4.40 4.50 e 2.54 BSC. E 7.00 BSC. E1 6.10 6.20 6.30 H 0.55 0.65 0.75 L 1.17 1.27 1.37 p 1.80 — 2.60 R 0.70 REF aaa 0.15 bbb 0.15 ccc 0.10	С	0.50	0.60	0.70
e 2.54 BSC. E 7.00 BSC. E1 6.10 6.20 6.30 H 0.55 0.65 0.75 L 1.17 1.27 1.37 p 1.80 — 2.60 R 0.70 REF 333 343 bbb 0.15 0.15 0.10 ddd 0.10 0.10 0.10	D	5.00 BSC		
E 7.00 BSC. E1 6.10 6.20 6.30 H 0.55 0.65 0.75 L 1.17 1.27 1.37 p 1.80 — 2.60 R 0.70 REF 333 0.15 bbb 0.15 0.10 0.10	D1	4.30	4.40	4.50
E1 6.10 6.20 6.30 H 0.55 0.65 0.75 L 1.17 1.27 1.37 p 1.80 — 2.60 R 0.70 REF 333 345 aaa 0.15 0.15 0.10 ddd 0.10 0.10 0.10	е	2.54 BSC.		
H 0.55 0.65 0.75 L 1.17 1.27 1.37 p 1.80 — 2.60 R 0.70 REF aaa 0.15 bbb 0.15 ccc 0.10 ddd 0.10	E	7.00 BSC.		
L 1.17 1.27 1.37 p 1.80 — 2.60 R 0.70 REF aaa 0.15 bbb 0.15 ccc 0.10 ddd 0.10	E1	6.10	6.20	6.30
p 1.80 — 2.60 R 0.70 REF aaa 0.15 bbb 0.15 ccc 0.10 ddd 0.10	Н	0.55	0.65	0.75
R 0.70 REF aaa 0.15 bbb 0.15 ccc 0.10 ddd 0.10	L	1.17	1.27	1.37
aaa 0.15 bbb 0.15 ccc 0.10 ddd 0.10	р	1.80		2.60
bbb 0.15 ccc 0.10 ddd 0.10	R	0.70 REF		
ccc 0.10 ddd 0.10	aaa	0.15		
ddd 0.10	bbb	0.15		
	CCC	0.10		
0.50	ddd	0.10		
0.00	eee	0.50		

Table 11. Package Diagram Dimensions (mm)



10

5. 6-Pin PCB Land Pattern

Figure 3 illustrates the 6-pin PCB land pattern for the Si550. Table 12 lists the values for the dimensions shown in the illustration.

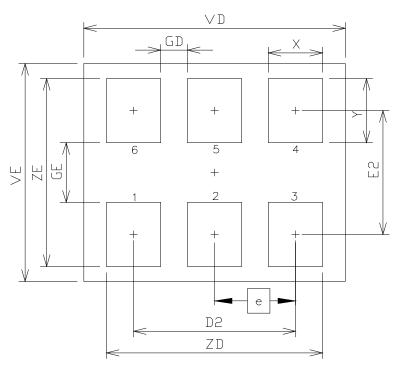


Figure 3. Si550 PCB Land Pattern

Table 12.	. PCB Land	Pattern Dime	ensions (mm)
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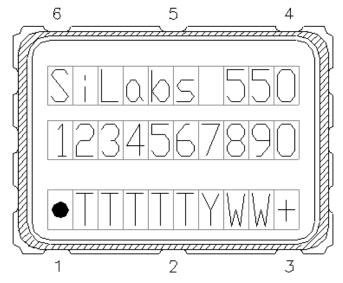
Dimension	Min	Max	
D2	5.08 REF		
е	2.54	2.54 BSC	
E2	4.15	4.15 REF	
GD	0.84		
GE	2.00		
VD	8.20 REF		
VE	7.30 REF		
Х	1.70 TYP		
Y	2.15 REF		
ZD	—	6.78	
ZE	—	6.30	
 Notes: 1. Dimensioning and tolerancing per the ANSI Y14.5M-1994 specification. 2. Land pattern design based on IPC-7351 guidelines. 			

- 3. All dimensions shown are at maximum material condition (MMC).
- **4.** Controlling dimension is in millimeters (mm).



6. Top Marking

6.1. Si550 Top Marking



6.2. Top Marking Explanation

Line	Position	Description		
1	1–10	"SiLabs"+ Part Family Number, 550 (First 3 characters in part number)		
2	1–10	Si550: Option1+Option2+Freq(6007)+Temp		
3	Trace Code			
	Position 1	Pin 1 orientation mark (dot)		
	Position 2	Product Revision (D)		
	Position 3–6	Tiny Trace Code (4 alphanumeric characters per assembly release instructions)		
	Position 7	Year (least significant year digit), to be assigned by assembly site (ex: $2010 = 0$)		
	Position 8–9	Calendar Work Week number (1–53), to be assigned by assembly site		
	Position 10	"+" to indicate Pb-Free and RoHS-compliant		



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DOCUMENT CHANGE LIST

Revision 0.6 to Revision 1.0

- Updated Table 4 on page 3.
 - Updated 2.5 V/3.3 V and 1.8 V CML output level specifications.
- Updated Table 5 on page 4.
 - Removed the words "Differential Modes: LVPECL/LVDS/CML" in the footnote referring to AN256.
 - Added footnotes clarifying max offset frequency test conditions.
 - Added CMOS phase jitter specs.
- Updated Table 9 on page 7.
 - Separated 1.8 V, 2.5 V/3.3 V supply voltage specifications.
- Updated and clarified Table 8 on page 7
 - Added "Moisture Sensitivity Level" and "Contact Pads" rows.
- Updated 6. "Top Marking" on page 12 to reflect specific marking information (previously, figure was generic).
- Updated 4. "Package Outline and Suggested Pad Layout" on page 10.
 - Added cyrstal impedance pin in Figure 2 on page 10 and Table 11 on page 10.
- Reordered spec tables and back matter to conform to data sheet quality conventions.



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